

Description

This invention relates to a chemical vapor deposition apparatus and a method of its use.

In the art of manufacturing semiconductor devices, it has long been a practice to employ chemical vapor deposition equipment for depositing various materials on substrates at high temperatures. Chemical vapor deposition equipment includes a reaction chamber configured to contain and control the flow of a reactant and carrier gas therethrough. A base, referred to as a susceptor, is located in the reaction chamber for supporting the substrates upon which the material is to be deposited; the reaction chamber, the susceptor and the substrate are heated to a desired reaction temperature.

A type of prior art structure (US-A-3 836 751) discloses a slablike susceptor fixedly supported in a horizontal reaction chamber to support a multiplicity of substrates or wafers. A first radiant heat source is located above the reaction chamber and includes a plurality of elongated parallel radiant heating elements lying along horizontal axes above the reaction chamber. A second radiant heat source is located below the reaction chamber and includes a plurality of elongated parallel radiant heating elements lying along horizontal axes transverse to the axis of the first radiant heat source. Thermal sensors are located in the susceptor to monitor the temperatures in various regions of the susceptor. The thermal sensors produce signals indicative of the temperatures sensed in their respective regions. Appropriate circuits and controls, responsive to the sensors, adjust the temperatures of the first and second radiant heat sources in the various regions to produce a substantially flat temperature profile in the susceptor.

While simultaneous deposition of materials on a multiplicity of substrates is desirable from a manufacturing standpoint, it has some drawbacks from a quality standpoint. The first problem associated with multi-substrate processing relates to the carrier gas which contains the atoms of the deposition materials. As the reactant gas flows over the surfaces of the substrate and the susceptor, deposition of the materials results in changes in the concentration of the deposition materials in the carrier gas. Consequently, as the reactant gas flows across the susceptor, any individual substrate and multiplicity of substrates, different rates of growth of the deposition of material may occur. A second problem is that of temperature control, which control is critical at the elevated temperatures needed for proper deposition. It is difficult, if not impossible, to control the temperature within the critical tolerances at all the desired locations within the relatively large reaction chambers. This results in different deposition layer thicknesses

from one substrate to another and can even produce varying thickness of deposition between individual substrates. Still another problem is contamination which can result from various factors such as: the handling techniques used to load and unload the substrates; the reactant and carrier gases, and the reaction chamber itself. The reactant gas not only deposits the material on the substrate but also on the walls of the reaction chamber. In the relatively large reaction chambers required for multisubstrate processing, the unwanted wall deposits can be inadvertently incorporated into the layers being deposited on the substrates.

These problems and other factors all contribute to significant problems as the semiconductor devices produced from the substrates and the uses to which they are put become more sophisticated. Consequently, many changes and improvements have been made in the equipment that is used to process simultaneously a multiplicity of substrates. For example, some equipment manufacturers are now using automated loading and unloading devices to eliminate contamination resulting from human handling. However, there are practical limits which many feel will ultimately make the simultaneous multisubstrate processing techniques unacceptable. One of the limitations is that of adapting the equipment to handle larger diameter substrates. The economics attendant large diameter substrates are beneficial. Increasing the size of the substrate results in problems with regard to temperature differentials across the substrate, decreasing concentrations of the deposition materials across the substrate and the like. Therefore, steps have been taken by some equipment manufacturers to make single substrate processing equipment significantly simpler in controlling the various factors involved in chemical vapor deposition. Single substrate processing is more desirable than multisubstrate equipment for large substrates, i.e. 15.24 to 20.32 centimeters (six to eight inches) and more in diameter. One important consideration is the cost at risk when processing one instead of several substrates; that is, if something goes wrong, the monetary loss is far less with one substrate than it is with a plurality of substrates.

GB-A-2 181 459 discloses the provision of two separate heaters and a single substrate susceptor capable of being rotated.

Accordingly, it is an object of the present invention to provide a heating system for the reaction chamber of chemical vapor deposition equipment.

Another object of the present invention is to provide a heating system for use in a horizontal flow reaction chamber having a rotatably driven circular susceptor mounted therein with a master temperature sensor proximate the center of the susceptor and slave temperature sensors mounted

at various points about the susceptor in a non rotating ring concentric with the susceptor.

Another object of the present invention is to provide a heating system for a reaction chamber having an upper heating element assembly located above the reaction chamber, a lower heating element assembly below the reaction chamber and a heat concentrator means for directing concentrated heat at the center of a rotatable susceptor.

Another object of the present invention is to provide a heating system for a reaction chamber having an upper heating element assembly of a plurality of elongated tube type radiant heating elements disposed along axes parallel with the flow of reactant gas through the reaction chamber and interacting with a special configuration of planar and curved reflective surfaces to provide a heat radiation pattern ideally suited for a rotatable circular susceptor.

Another object of the present invention is to provide a heating system for a reaction chamber having a lower heating element assembly of a plurality of elongated tube type radiant heating elements disposed along axes transverse to the flow of reactant gas through the reaction chamber and interacting with a special configuration of planar and curved reflective surfaces to provide a heat radiation pattern ideally suited for a rotatable susceptor.

Another object of the present invention is to provide upper and lower heating element assemblies and a concentrator means interacting with master and slave temperature sensors and a control circuit means for producing a flat temperature profile for a substrate supported on a susceptor in a reaction chamber.

These objects are achieved by the apparatus and method in accordance with Claims 1 and 15.

The chemical vapor deposition apparatus includes a horizontal flow reaction chamber having a bottom surface with a tubular shaft depending therefrom. A circular susceptor for supporting a single substrate is disposed within the reaction chamber on a driveshaft assembly which axially depends from the susceptor through the tubular shaft. The driveshaft assembly is rotatably drivable to rotate the susceptor and the supported substrate. The critical temperatures at various points of the susceptor are sensed by a master temperature sensor extending axially through the driveshaft assembly into the vicinity of the center of the susceptor. A special non rotatable ring is located in the reaction chamber in concentric relationship with the susceptor. At least one and preferably three or more slave temperature sensors are located in the fixed ring for sensing the temperatures at various points near the periphery of the susceptor. The master temperature sensor and the slave tempera-

ture sensors produce signals indicative of the temperatures sensed. These signals are transmitted to a control means which compares them to a predetermined set point temperature and generates signals coupled to a special heating system for controlling its operation.

The heating system includes an upper heating element assembly disposed above the reaction chamber, a lower heating element assembly located below the reaction chamber and a heat concentrator means. The upper heating element assembly includes a housing having a plurality of elongated tube type radiant heating elements which lie on horizontal axes in alignment with the direction of the reactant gas flow through the reaction chamber. The housing includes a combination of planar and curved reflective surfaces to provide a particular heat radiation pattern ideally suited for the susceptor and the fixed ring temperature sensor. The lower heating element assembly includes a housing having a plurality of elongated tube type radiant heating elements which lie along horizontal axes aligned transverse to the direction of the reactant gas flow through the reaction chamber. The housing includes a combination of planar and curved reflective surfaces to provide a heat radiation pattern ideally suited for the susceptor and the fixed ring temperature sensor.

A radiant heat concentrator means is mounted on the housing of the lower heating element assembly proximate the central opening thereof for directing concentrated radiant heat toward the center of the susceptor to compensate for heat losses due to the depending tubular shaft. In addition, the radiant heat concentrator means in combination with selected heat input zones of the upper and lower heating element assemblies provides a temperature controlling capability to allow a rapid build-up in the temperature of the susceptor at the beginning of a deposition cycle and a rapid temperature attenuation at the end of a deposition cycle. The master temperature sensor produces signals indicative of the changes in temperature and the control circuitry means reacts to those signals by appropriately changing the radiant heat output of the other heat input zones of the upper and lower heating element assemblies. The slave temperature sensors react to the temperature changes resulting from the changes in the heat output of the other heat input zones of upper and lower heating element assemblies by producing signals which are fed back to the control circuitry means which controls those other heat input zones of the upper and lower heating elements to provide a balancing effect to obtain a uniform temperature profile in the substrate or wafer.

The present invention will be more fully understood from the following description in conjunction

with the accompanying drawings.

Brief Description of the Drawings:

Figure 1 is a perspective view of a heating system shown in exploded relationship with a specialized reaction chamber, a rotatable circular susceptor and a temperature sensing arrangement for a chemical vapor deposition system.

Figure 2 is an enlarged sectional view taken along lines 2-2 of Figure 1 and shows the various features of the upper heating element assembly and its relationship to a reaction chamber, a rotatable circular susceptor and a temperature sensing arrangement of a deposition system.

Figure 3 is an enlarged sectional view taken along lines 3-3 of Figure 1 and shows the various features of the lower heater element assembly and the heat concentrator means and their relationship to a reaction chamber, a rotatable circular susceptor and a temperature sensing arrangement of a deposition system.

Figure 4 is an enlarged fragmentary sectional view taken along lines 4-4 of Figure 3.

Figure 5 is an enlarged fragmentary sectional view taken along lines 5-5 of Figure 1.

Figure 6 is a diagrammatic view of the heating system of the present invention and also shows an electrical schematic.

Description of the Preferred Embodiment:

The system illustrated in Figure 1 includes a reaction chamber 10 of the horizontal flow type formed of a material transparent to radiant heat energy, such as fused quartz. The reaction chamber includes a planar top wall 12, a planar bottom wall 14 with a tubular shaft 16 depending therefrom and the chamber defines a gas flow passage 17. A reactant gas flows within reaction chamber 10 in a direction indicated by the arrow 18 to deposit materials on a substrate 19 (Figures 2 and 3) placed in the reaction chamber at the beginning of a deposition cycle and removed therefrom after the cycle is completed.

The substrate is supported on susceptor 20. The susceptor is circular and is supported on and rotatably driven by a driveshaft assembly 22 extending downwardly from reaction chamber 10 and coaxially through tubular shaft 16. Temperature sensors include a master temperature sensor 24 extending axially upwardly through the driveshaft assembly for sensing the temperature at the center of the susceptor to produce signals indicative of the temperature sensed. A fixed, non rotating ring 26 is supported in reaction chamber 10 in concentric relationship with the susceptor. The fixed ring contains a plurality of slave temperature sensors

28, 29 and 30. The slave temperature sensors sense the temperatures at various points about the periphery of the susceptor and produce signals indicative of the temperatures sensed.

The heating system includes an upper heating element assembly 32, a lower heating element assembly 34 and a heat concentrator means 36. The upper heating element assembly includes a generally rectangular housing 38 having a planar top wall 40, a spaced apart pair of sidewalls 41 and 42 and a spaced apart pair of endwalls 44 and 46 which cooperatively define a downwardly opening chamber. A plurality of elongated tube type radiant heating elements 48A, 48B, 48C and 48D are mounted in the downwardly opening chamber and disposed in spaced apart parallel relationship and lie on an axis substantially parallel with the reactant gas flow path through reaction chamber 10. Each of the elongated tube type heating elements is preferably a high intensity tungsten filament lamp having a transparent quartz envelope containing a halogen gas, such as iodine. Elongated tube type heating elements, hereinafter referred to as lamps, 48A, 48B, 48C and 48D produce radiant heat energy of short wavelength (preferably on the order of 10^{-6} meters (one micron)) transmitted through the reaction chamber walls without appreciable absorption.

Although lamps 48A, 48B, 48C and 48D (hereinafter referred to as lamps) may be of different wattages, they are of similar configuration. The following description of one of lamps 48C and its mounting will be understood to apply to the other lamps as well. As shown best in Figure 5, the lamp has an integrally formed axially extending lug 50 on each of its opposite ends and a suitable connection pin arrangement 51 extends from each of the lugs for receiving connectors 52 provided at the ends of electrical conductors. Endwalls 44 and 46 of housing 38 are formed with downwardly opening slots 54 through which lugs 50 extend and shock pads 55 and 56 are mounted in the slots above and below the lugs. The lugs and the shock pads are demountably retained in their respective slots 54 by fastener means 58 (such as the illustrated offset screw washer device).

As shown in Figure 2, elongated linear concave reflective surfaces 59 and 60, which may be parabolic or elliptical segments in cross section, are provided above lamps 48A and proximate sidewall 41. Two similar elongated linear concave reflective surfaces 61 and 62 are provided above lamps 48D and proximate sidewall 42. Reflective surfaces 59, 60, 61 and 62 may be formed integral with top wall 40 or may be formed as separate elements which are welded or otherwise mounted in housing 38. Lamps 48A are located at the focal point of their respective reflective surfaces 59 and 60 so that the

radiated heat energy will be reflected along parallel paths, as indicated by the arrows. Similarly, lamps 48D are located at the focal points of their respective reflective surfaces 61 and 62 to produce parallel reflected radiant heat energy, as indicated. The reflected radiant heat energy is directed to the vicinity of fixed ring 26 and concentrates radiated heat energy in the vicinity of diametrically opposed lateral edges of susceptor 20 to compensate for heat losses which inherently occur there and at the peripheries of the susceptor and the supported substrate.

The exposed planar portion of inner surface 64 of top wall 40 is highly reflective (polished, plated or the like) so that both direct and reflected radiant heat energy from lamps 48B and 48C will be directed through top wall 12 of reaction chamber 10 and impinge on the upper surface of fixed ring 26, susceptor 20 and on supported substrate 19. The radiant energy which is directed onto the substrate will be of a more diffuse nature than the concentrated energy directed onto the fixed ring.

Lower heating element assembly 34 is similar to upper heating element assembly 32 and includes a generally rectangular housing 66 having a planar bottom wall 68, a spaced apart pair of sidewalls 70 and 72 and a spaced apart pair of endwalls 74 and 76 which cooperatively define an upwardly opening chamber. A plurality of elongated tube type radiant heating elements or lamps 78A, 78B, 78C and 78D are mounted in the upwardly opening chamber of housing 66 in spaced apart parallel relationship with respect to each other and on an axis transverse to the reactant gas flow path through reaction chamber 10; they are also transverse to lamps 48A-48D of the upper heating element assembly.

Each of lamps 78A, 78B, 78C and 78D may be identical with lamps 48A-48D. Further, lamps 78A-78D may be mounted in housing 66 in the manner hereinbefore described with reference to lamps 48A-48D.

As shown in Figure 3, elongated linear concave reflective surfaces 80 and 82, which may be parabolic or elliptical segments in cross section, are provided immediately below two lamps 78A proximate endwall 74 of housing 66. Two reflective surfaces 84 and 86 are located below two lamps 78D proximate sidewall 76 of the housing. Reflective concave surfaces 80, 82, 84 and 86 may be formed integrally in bottom wall 68 or may be formed as separate elements and mounted in the housing, as shown. Reflective concave surfaces 80, 82, 84 and 86 cooperate with their respective lamps 78A and 78D, located at the focal points of the reflective surfaces, to produce parallel rays of radiant heat energy into the vicinity of and onto fixed ring 26; this radiant energy cooperates with

the directly radiated heat energy to concentrate the radiated heat energy at the diametrically opposed peripheral edges of susceptor 20 at the upstream, or leading, edge of the susceptor and at the downstream, or trailing edge, of the susceptor.

The exposed planar portion of inner surface 88 of bottom wall 68 is highly reflective and both direct and reflected radiant heat energy from heat lamps 78B and 78C is directed through bottom wall 14 of reaction chamber 10 to heat fixed ring 26 and susceptor 20. Accordingly, the radiant energy directed onto the lower surface of the susceptor will be diffused.

Radiant heat energy from the upper heating element assembly 32 will heat fixed ring 26, susceptor 20 and substrate 19 from the top and the lower heating element assembly 34 will do the same from the bottom. Furthermore, by virtue of elongated concave reflective surfaces 59, 60, 61 and 62 of heating element assembly 32, concentrated heating zones or regions are provided in the vicinity of the diametrically opposed side edges, i.e. those adjacent the sidewalls of the reaction chamber. Similarly, by virtue of elongated concave reflective surfaces 80, 82, 84 and 86 of lower heating element assembly 34, transverse concentrated heating zones or regions are provided in the vicinity of the diametrically opposed front and back edges.

Bottom wall 68 of housing 66 is provided with a central opening 90 through which depending tubular shaft 16 and the susceptor supporting driveshaft assembly 22 extend. Due to the depending tubular shaft and the driveshaft assembly, there will be some inherent heat losses at the center of susceptor 20. To compensate for this heat loss and to provide temperature control, radiant heat concentrator means 36 is provided. The radiant heat concentrator means preferably includes four identical heat focusing devices 92, 94, 96 and 98 which are located in equally spaced apart relationship about vertical axis 100 (Figure 4) defined by central opening 90. Each of the heat focusing devices is attached to the bottom wall of lower housing 66.

As shown in Figure 4, radiant heat focusing device 98 (as well as 92, 94, 96) includes a cylindrical body 102 defining an open ended axial bore 104. The body is disposed so that axis 106 of the body forms an angle with respect to vertical axis 100 on the order of about 35°. Top end 108 of body 102 is of irregular configuration to fit into the irregular opening 90 of housing 66, to provide a noninterfering fit with the similar bodies of adjacent heating devices 92, 96 and to provide clearance for depending tubular shaft 16 of the reaction chamber. The lower end of body 102 has an extending tail portion 110 with an elongated opening 112. An L-shaped bracket 114 is provided with a first flange

116 having an internally threaded opening 118 for threadingly receiving a fastener bolt 120 to secure the L-shaped bracket to the tail portion of the body. By virtue of elongated opening, the entire L-shaped bracket can be adjustably moved axially toward and away from body 102. L-shaped bracket 114 includes a second flange or base 122 which lies in a plane transverse to axis 106. A lamp socket 124 is mounted on flange 122 to extend normally therefrom toward axial bore 104 of body 102. A bulb type radiant heating element, such as a lamp, 126 is mounted in socket 124 and extends axially upwardly into bore 104. The lamp is preferably a high intensity bulb having a tungsten filament 128 in a transparent quartz envelope filled with a suitable halogen gas.

L-shaped bracket 114 is also provided with a bore 130 parallel to but laterally offset from axis 106 of body 102. A rod 132 is axially slidable in bore 130 and a set screw 134 is employed to releasably hold the rod in position. The rod has a threaded upper end 135 mounted in a threaded bore formed in base 136 of a dish shaped reflector 138. The reflector is cylindrical and has a concave reflective surface 140 and a reflector axis 141 normal to base 136 and coincident with axis 106 of the body. The concave reflective surface may be parabolic or elliptical. An opening 142 extends axially from base 136 of the reflective surface and lamp 126 extends axially through opening 142 up into the area defined by concave reflective surface 140.

Lamp 126 is located to position its filament along the reflector axis proximate the focal point of reflector 138 so that the radiant heat energy impinging on the concave reflective surface will be convergently reflected. As the focal point of reflector 138 is a point and as the filament of the lamp is linear, the entire source of radiant heat energy cannot physically lie on the focal point. Therefore, the convergently reflected heat energy will not converge at a single point but will instead converge in an area which is a fuzzy concentration of radiated heat energy. As a result of such fuzzy concentration of radiated heat energy from each of focusing devices 92, 94 and 98, an area in and around the center of the susceptor 20 is the recipient of the concentrated heat energy; the radiation concentration can be adjustably varied due to the axially adjustable capabilities of the reflector and lamp 126.

Reference is now made to Figure 6 wherein a schematic diagram to illustrate a preferred manner of operation and control of the heating system of the present invention. Master heat sensor 24 and the temperature follower, or slave, heat sensors 28, 29 and 30, sense the temperatures at various zones in and around susceptor 20 and fixed ring 26

and produce signals indicative of the temperatures sensed. The signals from the master temperature sensor are directed to transmitter circuitry 150, as indicated at TCM. Similarly, signals from temperature sensors 28, 29 and 30, which may vary in number as needed, are supplied as inputs TF1, TF2, TF3...TFK, to transmitter circuitry 150. The transmitter circuitry contains well known components and circuits for transmitting the temperature indicative signals to an electronic heater control 152, as indicated by the data transfer arrow 153. Electronic heating control 152 may include any conventional type of master-slave heater control circuitry which would typically include a power supply, a plurality of lamp driver circuits and a plurality of differential amplifiers with selectively alterable offset controls.

Temperature control information, such as data indicating the start and finish of a vapor deposition cycle, the desired operating temperature at which the deposition is to be accomplished, and the like, may be supplied to the electronic heating control 152 from a temperature control means 154. The electronic heater control also receives data from temperature sensors 24, 28, 29 and 30. With this data, it generates a plurality of control signals to add or subtract power from upper and lower heating element assemblies 32 and 34 and concentrator means 36 for precise control of the heating of the susceptor. As the temperature sensors sense temperatures in various zones in reaction chamber 10, the radiant heat input of upper and lower heating element assemblies and the heat concentrator means can be operated in a manner to individually control zones of radiant heating energy.

As shown in Figure 6, the four lamps (48A and 48D) of upper heating element assembly 32 have their opposite end terminals connected together by conductors 160 and 162 to operate as an entity through control signals TC-3 from heater control 152. Thus, the four lamps provide two physically spaced apart commonly controlled heating zones proximate the opposite sidewalls of the reaction chamber; and the zones extend parallel with the reactant gas flow path and heat the opposed lateral edges of fixed ring 26 and susceptor 20. Two lamps 48B have their opposite end terminals connected together by conductors 164 and 166 and are controlled as an entity through control signals TC-2 from heater control 152. These two lamps provide two more physically separated heating zones which are controlled as a single entity; these zones extend parallel with the reactant gas flow path between the zones established by lamps 48A and 48D. Three lamps 48C have their opposite end terminals connected by conductors 168 and 170 to operate as an entity through control signals TC-1. These centrally located lamps provide a single

central zone of radiant heating energy which extends across fixed ring 26 and susceptor 20 parallel with the reactant gas flow path through the reaction chamber.

Lower heating element assembly 34 has the end terminals of two lamps 78A connected together by conductors 172 and 174 to operate as a single entity through control signals TC-7. These two lamps provide a single individually controllable zone of radiant heat energy extending transversely of the reaction chamber below the leading edges of fixed ring 26 and susceptor 20. Similarly, two lamps 78D have their end terminals connected together by conductors 176 and 178 to operate as an entity through control signals TC-7. These two lamps provide a single individually controllable zone of radiant heat energy extending transversely across the reaction chamber below the trailing edges of fixed ring 26 and susceptor 20. Two lamps 78B of lower heating element assembly 34 have their end terminals connected together by conductors 180 and 182 to operate as an entity by through control signals TC-6. These two lamps provide two spaced apart transversely extending zones of radiant heat energy controlled in unison; one of these zones is adjacent and immediately downstream of the leading edges of the fixed ring and the susceptor and the other zone is immediately upstream of trailing edges thereof. Similarly, two lamps 78C have their end terminals connected together by conductors 184 and 186 to operate as a single entity through control signals TC-5. These two lamps provide two physically spaced apart transversely extending heating zones disposed on opposite sides of the center of susceptor 20. Lamps 126 of heat concentrator means 36 have their respective terminals connected by conductors 188, 190, 192 and 194 connected to receive control signals TC-4. Thus, each of the radiant heat focusing devices operate in unison to provide a concentrated radiant energy heat zone at the center area of the susceptor.

Preferred Operation

When an input signal is received from temperature control input means 154 to indicate the start of a deposition cycle, heater control means 152 responds by applying full power to: radiant heat focusing devices 92, 94, 96 and 98 of the heat concentrator means 36; lamps 48B, 48C of upper heating assembly 32; and, lamps 78B, 78C of lower heating assembly 34. The same input signal contains information indicative of a desired operating temperature at which the deposition cycle is to be accomplished. The application of full power to heat concentrator means 36 and to the selected heating elements of heating assemblies 32 and 34 pro-

duces a rapid rise in the temperature in the central area of susceptor 20 and in the central area of substrate 19 being processed. Master temperature sensor 24 senses the rapid rise in temperature and sends signals indicative thereof to heater control means 152 which compares the sensed temperature with the desired operating temperature and adjusts the power supplied to concentrator means 36 and the selected lamps of upper and lower radiant heating assemblies 32 and 34 to produce and maintain the desired operating temperature in the central area of the susceptor and the substrate.

The sensed temperature signals produced by the master temperature sensor are also used simultaneously by heater control means 152 to apply power to lamps 48A, 48D, 78A and 78D of upper and lower heating element assemblies 32 and 34, respectively. Thus, while the temperature in the central areas of the susceptor and the substrate are being brought up to the desired operating temperature, the temperatures about the periphery of the susceptor and in fixed ring 26 are simultaneously being brought up to temperature by lamps 48A, 48D, 78A and 78D. The increasing temperatures in the peripherally located heating zones are sensed by slave temperature sensors 28, 29 and 30 and additional sensors, if desired. The signals received by heater control means 152 from slave temperature sensors 28, 29 and 30 are compared with the signal received from the master temperature sensor to adjust the power to lamps 48A, 48D, 78A and 78D to bring the temperatures in the peripherally located heating zones into alignment with the temperature in the central area of susceptor 20 and substrate 19.

Due to variables such as heat losses at the peripheral edges of substrate 19 and susceptor 20, the flow of reactant gas through reaction chamber 10 and the like, lamps 48A, 48D, 78A and 78D may be ideally set to normally operated at temperatures which are offset, i.e., different than the desired operating temperature in the central area of the substrate and the susceptor. The process of sensing temperatures and adjusting the power applied to the various groups or banks of heating elements as needed is continued throughout the deposition cycle. The object is to provide a uniform or flat temperature gradient in all of the relevant areas of the substrate, the susceptor and the fixed ring during the deposition cycles. In the interests of production time, it is preferable to bring the system up to temperature as fast as possible at the beginning of a cycle and to cool it down when a cycle is completed. The rapid increase in temperature at the beginning of a cycle is accomplished by heat concentrator means 36 and selected heating elements of upper and lower heating assemblies 32 and 34 in combination with the master-slave tem-

perature sensor arrangement which effectively produces a temperature following mode of operation. Cooling the system down at the end of a cycle is accomplished by reversing the above heating procedure. In other words, the power applied to concentrator means 36 and the selected heating elements proximate the center of upper and lower heating assemblies 32 and 34 is reduced and the temperature in the peripherally located heating zones will follow along with the reduction of heat at the center areas of the substrate and the susceptor.

Claims

1. A chemical vapor deposition apparatus having a susceptor for supporting a substrate within a reaction chamber and subject to the flow of a reactant gas through the reaction chamber, a heating apparatus for heating the substrate in a temperature controlled environment, said heating apparatus comprising in combination:

- a) a first plurality of radiant heat energy sources having a first longitudinal axis for radiating heat upon the top surface of the substrate and the susceptor, said first plurality of sources capable of radiating greater heat energy at diametrically opposed generally peripheral areas than at central areas of the substrate and the susceptor;

- b) a second plurality of radiant heat energy sources having a second longitudinal axis orthogonal to the first longitudinal axis for radiating heat upon the bottom surface of the susceptor, said second plurality of sources capable of radiating greater heat energy at diametrically opposed generally peripheral areas than at a central area of the susceptor;

- c) a third radiant heat energy source for radiating heat energy upon the generally central bottom surface of the susceptor;

- d) means for sensing the temperature at a plurality of zones within the reaction chamber and for generating signals reflective of the temperatures sensed; and

- e) control means responsive to the signals generated by said temperature sensing means for varying the radiant heat energy emitted by said first plurality of radiant heat energy sources, said second plurality of radiant heat energy sources and said third radiant heat energy source to establish and maintain the substrate at predetermined temperatures during processing of the substrate.

2. The apparatus as set forth in Claim 1, wherein the longitudinal axis of one of said first and second plurality of radiant heat energy sources is axially oriented parallel with the flow of the reactant gas within the reaction chamber and the longitudinal axis of the other of said first and second plurality of radiant heat energy sources is axially oriented transverse with the flow of the reactant gas within the reaction chamber.

3. The apparatus as set forth in Claim 1, wherein the reaction chamber includes top and bottom panels transparent to the radiant heat energy emitted by said first and second plurality of radiant heat energy sources and to the radiant heat energy emitted by said third radiant heat energy source and wherein said first and second plurality of radiant heat energy sources and said third radiant heat energy source are disposed external to the reaction chamber and radiate heat energy through said top and bottom panels into the reaction chamber.

4. The apparatus as set forth in Claim 1, wherein said first plurality of radiant heat energy sources includes concave reflective surfaces for radiating greater heat energy upon the opposed peripheral areas than the central areas of the substrate and the susceptor.

5. The apparatus as set forth in Claim 1, wherein said second plurality of radiant heat energy sources includes concave reflective surfaces for radiating greater heat energy upon the opposed peripheral areas than the central areas of the substrate and the susceptor.

6. The apparatus as set forth in Claim 1, wherein said third radiant heat energy source includes concave reflective surfaces for radiating heat energy upon the central bottom surface of the susceptor.

7. The apparatus as set forth in Claim 1, including a fixed ring disposed about the peripheral edge of the susceptor onto which radiant heat energy is directed by said first and second plurality of radiant heat energy sources.

8. The apparatus as set forth in Claim 7, wherein said sensing means are mounted in the fixed ring for sensing the temperature at different locations about the periphery of the susceptor.

9. The apparatus as set forth in Claim 7, wherein said first and second plurality of radiant heat energy sources comprise discrete heating ele-



perature sensor arrangement which effectively produces a temperature following mode of operation. Cooling the system down at the end of a cycle is accomplished by reversing the above heating procedure. In other words, the power applied to concentrator means 36 and the selected heating elements proximate the center of upper and lower heating assemblies 32 and 34 is reduced and the temperature in the peripherally located heating zones will follow along with the reduction of heat at the center areas of the substrate and the susceptor.

Claims

1. A chemical vapor deposition apparatus having a susceptor for supporting a substrate within a reaction chamber and subject to the flow of a reactant gas through the reaction chamber, a heating apparatus for heating the substrate in a temperature controlled environment, said heating apparatus comprising in combination:
 - a) a first plurality of radiant heat energy sources having a first longitudinal axis for radiating heat upon the top surface of the substrate and the susceptor, said first plurality of sources capable of radiating greater heat energy at diametrically opposed generally peripheral areas than at central areas of the substrate and the susceptor;
 - b) a second plurality of radiant heat energy sources having a second longitudinal axis orthogonal to the first longitudinal axis for radiating heat upon the bottom surface of the susceptor, said second plurality of sources capable of radiating greater heat energy at diametrically opposed generally peripheral areas than at a central area of the susceptor;
 - c) a third radiant heat energy source for radiating heat energy upon the generally central bottom surface of the susceptor;
 - d) means for sensing the temperature at a plurality of zones within the reaction chamber and for generating signals reflective of the temperatures sensed; and
 - e) control means responsive to the signals generated by said temperature sensing means for varying the radiant heat energy emitted by said first plurality of radiant heat energy sources, said second plurality of radiant heat energy sources and said third radiant heat energy source to establish and maintain the substrate at predetermined temperatures during processing of the substrate.
2. The apparatus as set forth in Claim 1, wherein the longitudinal axis of one of said first and second plurality of radiant heat energy sources is axially oriented parallel with the flow of the reactant gas within the reaction chamber and the longitudinal axis of the other of said first and second plurality of radiant heat energy sources is axially oriented transverse with the flow of the reactant gas within the reaction chamber.
3. The apparatus as set forth in Claim 1, wherein the reaction chamber includes top and bottom panels transparent to the radiant heat energy emitted by said first and second plurality of radiant heat energy sources and to the radiant heat energy emitted by said third radiant heat energy source and wherein said first and second plurality of radiant heat energy sources and said third radiant heat energy source are disposed external to the reaction chamber and radiate heat energy through said top and bottom panels into the reaction chamber.
4. The apparatus as set forth in Claim 1, wherein said first plurality of radiant heat energy sources includes concave reflective surfaces for radiating greater heat energy upon the opposed peripheral areas than the central areas of the substrate and the susceptor.
5. The apparatus as set forth in Claim 1, wherein said second plurality of radiant heat energy sources includes concave reflective surfaces for radiating greater heat energy upon the opposed peripheral areas than the central areas of the substrate and the susceptor.
6. The apparatus as set forth in Claim 1, wherein said third radiant heat energy source includes concave reflective surfaces for radiating heat energy upon the central bottom surface of the susceptor.
7. The apparatus as set forth in Claim 1, including a fixed ring disposed about the peripheral edge of the susceptor onto which radiant heat energy is directed by said first and second plurality of radiant heat energy sources.
8. The apparatus as set forth in Claim 7, wherein said sensing means are mounted in the fixed ring for sensing the temperature at different locations about the periphery of the susceptor.
9. The apparatus as set forth in Claim 7, wherein said first and second plurality of radiant heat energy sources comprise discrete heating ele-



- ments with their longitudinal axes being generally evenly spaced apart and further comprise concave reflective surfaces for reflecting radiant energy from said elements in generally parallel paths onto said fixed ring.
10. The heating apparatus as set forth in Claim 9, wherein said control means includes means for modulating the radiant heat energy emitted by selected elements of said first and second plurality of radiant heat energy sources to adjust the temperature within the reaction chamber to conform with a predetermined temperature profile.
 11. The heating apparatus as set forth in Claim 10, wherein said control means includes means for modulating the radiant heat energy emitted by said third radiant heat energy source in conjunction with said selected elements to adjust the temperature within the reaction chamber to conform with a predetermined temperature profile.
 12. The apparatus as set forth in Claim 1, wherein said apparatus includes a rotatable drive shaft assembly concentric with and adapted to support said susceptor and extending upward through a bottom wall into said reaction chamber through a tubular shaft, said third radiant heat energy source compensates for the heat loss to the susceptor due to the drive shaft assembly and tubular shaft.
 13. The heating apparatus as set forth in Claim 12, wherein said third radiant heat energy source comprises a third plurality of heating elements generally focussed on a central bottom surface of said susceptor.
 14. The apparatus as set forth in Claim 12, wherein said drive shaft assembly is hollow and part of said sensing means extends through said hollow shaft assembly for sensing the temperature at the central bottom surface of the susceptor.
 15. A method performed in a chemical vapor deposition apparatus as claimed in Claims 1-14, wherein for uniformly heating the substrate in a temperature controlled environment, said method comprising steps of:
 - a) radiating heat upon the top surface of the substrate and the susceptor from a first plurality of radiant heat energy sources having a first longitudinal axis, said step of radiating including the step of radiating greater energy at diametrically opposed
 - generally peripheral areas than at central areas of the substrate and the susceptor;
 - b) radiating heat upon the bottom surface of the susceptor from a second plurality of radiant heat energy sources having a second longitudinal axis orthogonal to the first longitudinal axis, said step of radiating including the step of radiating greater energy at diametrically opposed generally peripheral areas than at a central area of the susceptor;
 - c) radiating heat energy from a third source upon the generally central bottom surface of the susceptor;
 - d) sensing the temperature at a plurality of zones within the reaction chamber and generating signals reflective of the temperatures sensed; and
 - e) varying the radiant heat energy emitted by the first plurality of sources, the second plurality of sources and the third source in response to the signals generated in said generating step to establish and to maintain the substrate at a uniform predetermined temperature during process of the substrate.
 16. The method as set forth in Claim 15, wherein said step of sensing includes the step of sensing the temperature about the susceptor at several locations.
 17. The method as set forth in Claim 15, including the step of reflecting the radiant heat energy from the first plurality of radiant heat energy sources toward the top surfaces of the substrate and the susceptor.
 18. The method as set forth in Claim 15, including the step of reflecting the radiant heat energy from the second plurality of radiant heat energy sources toward the bottom surface of the susceptor.
 19. The method as set forth in Claim 15, including the step of adjusting the radiant heat energy upon the bottom of the susceptor and emitted from the third radiant heat energy source.
 20. The method as set forth in Claim 15, wherein the step of varying the radiant heat energy emitted produces a rapid rise in temperature in the central regions of the substrate and susceptor at the beginning of a production cycle.
 21. The method as set forth in Claim 15, wherein the step of varying the radiant heat energy



emitted produces a rapid drop in temperature in the central regions of the substrate and susceptor at the end of a production cycle.

Patentansprüche

1. Chemische Dampfniederschlagsvorrichtung mit einem Träger zum Halten eines Substrats innerhalb der Reaktionskammer, das einer Strömung von Reaktionsgas durch die Reaktionskammer unterliegt, und einer Heizvorrichtung zum Beheizen des Substrats in einer temperaturgeregelten Umgebung, wobei die Heizvorrichtung in Kombination folgendes aufweist:

a) eine erste Mehrzahl von Wärmestrahlung-Energiequellen mit einer ersten Längsachse zum Abstrahlen von Wärme auf die Oberfläche des Substrats und des Trägers, wobei diese erste Mehrzahl von Quellen dazu in der Lage ist, in einander diametral entgegengesetzte Bereiche, die im wesentlichen Randbereiche sind, mehr zu strahlen als in die zentralen Bereiche des Substrats und des Trägers;

b) eine zweite Mehrzahl von Wärmestrahlung-Energiequellen mit einer zweiten Längsachse rechtwinklig zur ersten Längsachse zum Abstrahlen von Wärme auf die Bodenfläche des Trägers, wobei diese erste Mehrzahl von Quellen dazu in der Lage ist, in einander diametral entgegengesetzte Bereiche, die im wesentlichen Randbereiche sind, mehr zu strahlen als in den zentralen Bereich des Trägers;

c) eine dritte Wärmestrahlung-Energiequelle zum Abstrahlen von Wärmeenergie auf die im wesentlichen zentrale Bodenfläche des Trägers;

d) Einrichtungen zum Messen der Temperatur in mehreren Zonen innerhalb der Reaktionskammer und zum Erzeugen von Signalen, die die gemessenen Temperaturen widerspiegeln; und

e) eine Regelungseinrichtung, die auf die von den Temperaturmeßeinrichtungen erzeugten Signale anspricht, um die Wärmestrahlungsenergie zu verändern, wie sie durch die erste Mehrzahl von Wärmestrahlung-Energiequellen, die zweite Mehrzahl von Wärmestrahlung-Energiequellen und die dritte Wärmestrahlung-Energiequelle abgestrahlt wird, um das Substrat während der Verarbeitung desselben auf vorgegebene Temperaturen zu führen und auf diesen zu halten.

2. Vorrichtung nach Anspruch 1, bei der die Längsachse der einen der ersten und zweiten

Mehrzahl von Wärmestrahlung-Energiequellen axial parallel mit der Strömung des Reaktionsgases innerhalb der Reaktionskammer ausgerichtet ist und die Längsachse der anderen der ersten und zweiten Mehrzahl von Wärmestrahlung-Energiequellen axial quer zur Strömung des Reaktionsgases innerhalb der Reaktionskammer ausgerichtet ist.

3. Vorrichtung nach Anspruch 1, bei der die Reaktionskammer eine Decken- und eine Bodenplatte aufweist, die für die Wärmestrahlungsenergie, wie sie von der ersten und zweiten Mehrzahl von Wärmestrahlung-Energiequellen emittiert wird, und für die von der dritten Wärmestrahlung-Energiequelle emittierte Wärmestrahlungsenergie durchsichtig sind, und bei der die erste und die zweite Mehrzahl von Wärmestrahlung-Energiequellen und die dritte Wärmestrahlung-Energiequelle außerhalb der Reaktionskammer angeordnet sind und Wärmestrahlungsenergie durch die Decken- und Bodenplatte in die Reaktionskammer einstrahlen.

4. Vorrichtung nach Anspruch 1, bei der die erste Mehrzahl von Wärmestrahlung-Energiequellen konkave, reflektierende Flächen zum Abstrahlen von mehr Wärmeenergie auf die einander entgegengesetzten Randbereiche als auf die zentralen Bereiche des Substrats und des Trägers aufweist.

5. Vorrichtung nach Anspruch 1, bei der die zweite Mehrzahl von Wärmestrahlung-Energiequellen konkave, reflektierende Flächen zum Abstrahlen von mehr Wärmeenergie auf die einander entgegengesetzten Randbereiche als auf die zentralen Bereiche des Substrats und des Trägers aufweist.

6. Vorrichtung nach Anspruch 1, bei der die dritte Wärmestrahlung-Energiequelle konkave, reflektierende Flächen zum Abstrahlen von Wärmeenergie auf die zentrale Bodenfläche des Trägers aufweist.

7. Vorrichtung nach Anspruch 1, mit einem feststehenden Ring, der um die Randkante des Trägers angeordnet ist, auf den Wärmestrahlungsenergie durch die erste und zweite Mehrzahl von Wärmestrahlung-Energiequellen gerichtet wird.

8. Vorrichtung nach Anspruch 7, bei dem die Meßeinrichtungen im feststehenden Ring angeordnet sind, um die Temperatur an verschiedenen Orten um den Rand des Trägers zu mes-



sen.

9. Vorrichtung nach Anspruch 7, bei der die erste und zweite Mehrzahl von Wärmestrahlung-Energiequellen diskrete Heizelemente aufweist, deren Längsachsen im wesentlichen gleichmäßig voneinander beabstandet sind, und sie ferner konkave, reflektierende Flächen zum Reflektieren von Strahlungsenergie von den Elementen in im wesentlichen parallelen Pfaden auf den feststehenden Ring aufweist. 5 10
10. Heizvorrichtung nach Anspruch 9, bei der die Regelungseinrichtung eine Einrichtung zum Modulieren der Wärmestrahlungsenergie aufweist, wie sie von ausgewählten Elementen der ersten und zweiten Mehrzahl von Wärmestrahlung-Energiequellen emittiert wird, um die Temperatur innerhalb der Reaktionskammer so einzustellen, daß sie einem vorgegebenen Temperaturprofil genügt. 15 20
11. Heizvorrichtung nach Anspruch 10, bei der die Regelungseinrichtung eine Einrichtung zum Modulieren der Wärmestrahlungsenergie aufweist, wie sie von der dritten Wärmestrahlung-Energiequelle in Verbindung mit den ausgewählten Elementen emittiert wird, um die Temperatur innerhalb der Reaktionskammer so einzustellen, daß sie einem vorgegebenen Temperaturprofil genügt. 25 30
12. Vorrichtung nach Anspruch 1, die eine drehbare Antriebswellenanordnung konzentrisch zum Träger aufweist, die so ausgebildet ist, daß sie den Träger hält, und die sich durch eine Bodenwand durch einen rohrförmigen Schaft in die Reaktionskammer hinein erstreckt, wobei die dritte Wärmestrahlung-Energiequelle den Wärmeverlust am Träger aufgrund der Antriebswellenanordnung und des rohrförmigen Schafts kompensiert. 35 40
13. Heizvorrichtung nach Anspruch 12, bei der die dritte Wärmestrahlung-Energiequelle eine dritte Mehrzahl von Heizelementen aufweist, die im wesentlichen auf die zentrale Bodenfläche des Trägers fokussiert sind. 45
14. Vorrichtung nach Anspruch 12, bei der die Antriebswellenanordnung hohl ist und ein Teil der Meßeinrichtungen sich durch diese hohle Schaftanordnung erstreckt, um die Temperatur an der zentralen Bodenfläche des Trägers zu messen. 50
15. Verfahren, das in einer chemischen Dampfniederschlagsvorrichtung ausgeführt wird, wie sie

in den Ansprüchen 1 - 14 beansprucht wurde, wobei das Verfahren zum gleichmäßigen Aufheizen des Substrats in einer temperaturgeregelten Umgebung folgende Schritte aufweist:

- a) Einstrahlen von Wärme auf die Oberfläche des Substrats und des Trägers von einer ersten Mehrzahl von Wärmestrahlung-Energiequellen mit einer ersten Längsachse her, wobei dieser Schritt des Einstrahlens einen Schritt des Einstrahlens größerer Energie in einander diametral gegenüberstehenden Flächen, die im wesentlichen Randflächen bilden, als in die zentralen Bereiche des Substrats und des Trägers beinhaltet;
- b) Einstrahlen von Wärme auf die Bodenfläche des Trägers von einer zweiten Mehrzahl von Wärmestrahlung-Energiequellen mit einer zweiten Längsachse, die rechtwinklig zur ersten Längsachse steht, her, wobei der Schritt des Einstrahlens einen Schritt des Einstrahlens größerer Energie in einander diametral gegenüberstehenden Flächen, die im wesentlichen Randflächen bilden, als in den zentralen Bereich des Trägers beinhaltet;
- c) Einstrahlen von Wärmeenergie von einer dritten Quelle auf die im wesentlichen zentrale Bodenfläche des Trägers;
- d) Messen der Temperatur in mehreren Zonen innerhalb der Reaktionskammer und Erzeugen von Signalen, die die gemessenen Temperaturen reflektieren; und
- e) Verändern der Wärmestrahlungsenergie, wie sie von der ersten Mehrzahl von Quellen, der zweiten Mehrzahl von Quellen und der dritten Quelle emittiert wird, auf die im Erzeugungsschritt erzeugten Signale hin, um die Temperatur während der Bearbeitung des Substrats auf eine vorgegebene, gleichmäßige Temperatur zu bringen und dort zu halten.

16. Verfahren nach Anspruch 15, bei dem der Meßschritt den Schritt des Messens der Temperatur um den Halter an mehreren Orten umfaßt.

17. Verfahren nach Anspruch 15, mit dem Schritt des Reflektierens der Wärmestrahlungsenergie von der ersten Mehrzahl von Wärmestrahlung-Energiequellen zu den Oberflächen des Substrats und des Trägers.

18. Verfahren nach Anspruch 15, mit dem Schritt des Reflektierens der Wärmestrahlungsenergie von der zweiten Mehrzahl von Wärmestrahlung-Energiequellen zur Bodenfläche des Trägers.



gers.

19. Verfahren nach Anspruch 15, mit dem Schritt des Einstellens der Wärmestrahlungsenergie auf den Boden des Trägers, wie sie von der dritten Wärmestrahlung-Energiequelle emittiert wird. 5
20. Verfahren nach Anspruch 15, bei dem der Schritt des Veränderns der emittierten Wärmestrahlungsenergie einen schnellen Temperaturanstieg in den zentralen Bereichen des Substrats und des Trägers zu Beginn eines Herstellzyklus verursacht. 10
21. Verfahren nach Anspruch 15, bei dem der Schritt des Veränderns der emittierten Wärmestrahlungsenergie einen schnellen Temperaturabfall in den zentralen Bereichen des Substrats und des Trägers am Ende eines Herstellzyklus hervorruft. 15

Revendications

1. Appareil de dépôt chimique en phase vapeur ayant une base destinée à supporter un substrat placé dans une chambre de réaction et soumis à l'écoulement d'un gaz réactif à travers la chambre de réaction, et un appareil de chauffage destiné à chauffer le substrat dans un environnement à température contrôlée, ledit appareil de chauffage comprenant en combinaison : 25
 - a) une première pluralité de sources d'énergie thermique radiante ayant un premier axe longitudinal destinée à rayonner de la chaleur vers la surface supérieure du substrat et de la base, ladite première pluralité de sources étant capable de rayonner une plus grande énergie thermique dans des zones sensiblement périphériques diamétralement opposées que dans les zones centrales du substrat et de la base ; 30
 - b) une deuxième pluralité de sources d'énergie thermique radiante ayant un deuxième axe longitudinal orthogonal au premier axe longitudinal destinée à rayonner de la chaleur vers la surface inférieure de la base, ladite deuxième pluralité de sources étant capable de rayonner une plus grande énergie thermique dans des zones sensiblement périphériques diamétralement opposées que dans une zone centrale de la base ; 40
 - c) une troisième source d'énergie thermique radiante destinée à rayonner de l'énergie thermique vers la surface inférieure sensiblement centrale de la base ; 45
2. Appareil selon la revendication 1, dans lequel l'axe longitudinal d'une desdites première et deuxième pluralités de sources d'énergie thermique radiante est orientée axialement parallèlement à l'écoulement du gaz réactif dans la chambre de réaction, et l'axe longitudinal de l'autre desdites première et deuxième pluralités de sources d'énergie thermique radiante est orienté axialement transversalement à l'écoulement du gaz réactif dans la chambre de réaction. 50
3. Appareil selon la revendication 1, dans lequel la chambre de réaction comprend des panneaux haut et de fond transparents à l'énergie thermique radiante émise par lesdites première et deuxième pluralités de sources d'énergie thermique radiante et à l'énergie thermique radiante émise par ladite troisième source d'énergie thermique radiante, et dans lequel lesdites première et deuxième pluralités de sources d'énergie thermique radiante et ladite troisième source d'énergie thermique radiante sont disposées à l'extérieur de la chambre de réaction et rayonnent de l'énergie thermique qui pénètre dans la chambre de réaction à travers lesdits panneaux haut et de fond. 55
4. Appareil selon la revendication 1, dans lequel ladite première pluralité de sources d'énergie thermique radiante comprend des surfaces réfléchissantes concaves pour rayonner une plus grande énergie thermique vers les zones périphériques opposées que vers les zones centrales du substrat et de la base. 60
5. Appareil selon la revendication 1, dans lequel ladite deuxième pluralité de sources d'énergie thermique radiante comprend des surfaces réfléchissantes concaves pour rayonner une plus 65

d) des moyens destinés à capter la température dans une pluralité de zones à l'intérieur de la chambre de réaction et à engendrer des signaux qui reflètent les températures captées ; et

e) des moyens de commande qui répondent aux signaux engendrés par lesdits moyens capteurs de température en faisant varier l'énergie thermique radiante émise par ladite première pluralité de sources d'énergie thermique radiante, par ladite deuxième pluralité de sources d'énergie thermique radiante et par ladite troisième source d'énergie thermique radiante, pour porter et maintenir le substrat à des températures prédéterminées pendant le traitement du substrat.



grande énergie thermique vers les zones périphériques opposées que vers les zones centrales du substrat et de la base.

6. Appareil selon la revendication 1, dans lequel ladite troisième source d'énergie thermique radiante comprend des surfaces réfléchissantes concaves pour rayonner de l'énergie thermique vers la surface inférieure centrale de la base. 5
7. Appareil selon la revendication 1, comprenant un anneau fixe disposé autour du bord périphérique de la base, sur lequel l'énergie thermique radiante est projetée par lesdites première et deuxième pluralités de sources d'énergie thermique radiante. 10
8. Appareil selon la revendication 7, dans lequel lesdits moyens capteurs sont montés dans l'anneau fixe pour capter la température en différents points de la périphérie de la base. 15
9. Appareil selon la revendication 7, dans lequel lesdites première et deuxième pluralités de sources d'énergie thermique radiante comprennent des éléments chauffants discrets dont les axes longitudinaux sont espacés sensiblement uniformément et comprennent en outre des surfaces réfléchissantes concaves destinées à réfléchir l'énergie radiante issue desdits éléments vers l'anneau fixe, selon des trajets sensiblement parallèles. 20
10. Appareil de chauffage selon la revendication 9, dans lequel lesdits moyens de commande comprennent des moyens servant à moduler l'énergie thermique radiante émise par des éléments sélectionnés desdites première et deuxième pluralités de sources d'énergie thermique radiante afin d'ajuster la température régnant dans la chambre de réaction de façon qu'elle soit conforme à un profil de température prédéterminé. 25
11. Appareil de chauffage selon la revendication 10, dans lequel lesdits moyens de commande comprennent des moyens destinés à moduler l'énergie thermique radiante émise par la troisième source d'énergie thermique radiante en combinaison avec lesdits éléments sélectionnés pour ajuster la température régnant dans ladite chambre de réaction de façon qu'elle soit conforme à un profil de température prédéterminé. 30
12. Appareil selon la revendication 1, dans lequel ledit appareil comprend un ensemble d'arbre d'entraînement rotatif concentrique à ladite 35

base et adapté pour supporter cette base, et qui s'étend vers le haut à travers une paroi de fond pour pénétrer dans ladite chambre de réaction en passant dans un arbre tubulaire, ladite troisième source d'énergie thermique radiante compensant la perte de chaleur transmise à la base en raison de la présence de l'ensemble d'arbre d'entraînement et de l'arbre tubulaire.

13. Appareil de chauffage selon la revendication 12, dans lequel ladite troisième source d'énergie thermique radiante comprend une troisième pluralité d'éléments chauffants sensiblement focalisés sur la surface intérieure centrale de ladite base. 40
14. Appareil selon la revendication 12, dans lequel ledit ensemble d'arbre d'entraînement est creux et une partie desdits moyens capteurs passe à travers ledit ensemble d'arbre creux pour capter la température régnant à la surface inférieure centrale de la base. 45
15. Procédé mis en œuvre dans un appareil de dépôt chimique en phase vapeur selon les revendications 1 à 14, dans lequel, pour chauffer uniformément le substrat dans un environnement à température commandée, ledit procédé comprend les phases consistant à : 50
 - a) rayonner de la chaleur vers la surface supérieure du substrat et de la base en provenance d'une première pluralité de sources d'énergie thermique radiante ayant un premier axe longitudinal, ladite phase de rayonnement comprenant la phase consistant à rayonner une plus grande énergie dans des zones sensiblement périphériques diamétralement opposées que dans les zones centrales du substrat et de la base ;
 - b) rayonner de la chaleur vers la surface inférieure de la base en provenance d'une deuxième pluralité de sources d'énergie thermique radiante ayant un deuxième axe longitudinal orthogonal au premier axe longitudinal, ladite phase de rayonnement comprenant la phase consistant à rayonner une plus grande énergie vers des zones sensiblement périphériques diamétralement opposées que vers une zone centrale de la base ;
 - c) rayonner de l'énergie thermique en provenance d'une troisième source vers la surface inférieure sensiblement centrale de la base ;
 - d) capter la température dans une pluralité de zones à l'intérieur de la chambre de réaction et engendrer des signaux qui reflè-



tent les températures captées ; et
e) faire varier l'énergie thermique radiante émise par la première pluralité de sources, la deuxième pluralité de sources et la troisième source en réponse aux signaux engendrés dans ladite phase de génération, pour porter et maintenir le substrat à une température prédéterminée uniforme pendant le traitement du substrat.

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16. Procédé selon la revendication 15, dans lequel ladite phase de captage comprend la phase consistant à capter la température autour de la base en plusieurs points.

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17. Procédé selon la revendication 15, comprenant la phase consistant à réfléchir l'énergie thermique radiante émise par la première pluralité de sources d'énergie thermique radiante vers les surfaces supérieures du substrat et de la base.

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18. Procédé selon la revendication 15, comprenant la phase consistant à réfléchir l'énergie thermique radiante issue de la deuxième pluralité de sources d'énergie thermique radiante vers la surface inférieure de la base.

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19. Procédé selon la revendication 15, comprenant la phase consistant à régler l'énergie thermique radiante projetée sur la surface inférieure de la base et émise par la troisième source d'énergie thermique radiante.

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20. Procédé selon la revendication 15, dans lequel la phase consistant à faire varier l'énergie thermique radiante émise produit une élévation rapide de la température dans les régions centrales du substrat et de la base au début d'un cycle de production.

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21. Procédé selon la revendication 15, dans lequel la phase consistant à faire varier l'énergie thermique radiante émise produit une chute rapide de la température dans les régions centrales du substrat et de la base à la fin d'un cycle de production.

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